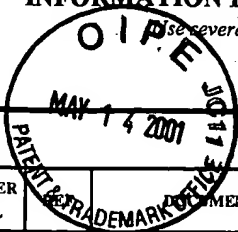


INFORMATION DISCLOSURE STATEMENT



Docket Number (Optional)

010456

Application Number

09/807,947

Applicant(s)

MEHR, Wolfgang

Filing Date

20 April 2001

Group Art Unit

2832

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
✓	A	0 116 702	8/19894	E.P.O.	H01L	21/31		✓
	B	0 859 402	8/1998	E.P.O.	H01L	21/28		✓
	C	55008026 *)	1/1980	Japan	H01L	29/04		✓
	D	59048952 *)	3/1984	Japan	H01L	27/04		✓
✓	E	01007549 *)	6/1987	Japan	H01L	27/04		✓

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

✓	aa	V.Z-Q Li et al., Structure and properties of rapid thermal chemical vapor deposited polycrystalline silicon-germanium films on SiO2 using Si2H6, GeH4 and B2H6 gases; J. Appl. Phys., Vol. 83, No. 10, 15 May 1998, pp. 5469-5476
		*) Patent Abstracts of Japan — NO TITLE, DATE ETC.

EXAMINER

✓

DATE CONSIDERED

5/14/02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.